

## C16-EC-105

## 6032

# BOARD DIPLOMA EXAMINATION, (C-16) OCT/NOV-2018

### **DECE—FIRST YEAR EXAMINATION**

ELECTRONIC DEVICES AND POWER SUPPLIES

Time : 3 hours ]

[ Total Marks : 80

#### PART—A

3×10=30

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**Instructions** : (1) Answer **all** questions.

- (2) Each question carries three marks.
- (3) Answers should be brief and straight to the point and shall not exceed *five* simple sentences.
- **1.** Define the term resistance.
- 2. List the specifications of inductor.
- 3. Define the terms dielectric strength and dielectric constant.
- 4. List different types of fuse.
- 5. List the materials used in screen printing for making PCB.
- **6.** Sketch the energy band diagrams for conductor, semiconductor and insulator materials.
- **7.** Sketch the *V*-*I* characteristics of a *P*-*N* diode.

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- **8.** Sketch the input characteristics of CB configuration.
- 9. Draw the drain characteristics of MOSFET (*n*-channel).
- **10.** Define voltage regulation.

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		<b>PART—B</b> 10	)×5=50	P.
Instructions : (1) Answer any five questions.				
		(2) Each question carries <b>ten</b> marks.	07.9	
		(3) Answers should be comprehensive and the cr for valuation is the content but not the ler the answer.	riterion 1gth of	
11.	(a)	Define temperature coefficient of resistance.	3	
	(b)	Describe the working of thermistor and sensitor and statheir applications.	ate 7	
12.	De	scribe the methods of etching, cleaning and drilling of PCE	3.	
13.	(a)	Compare among conductor, semiconductor and insulator	rs. 5	
	(b)	Explain valance, conduction and forbidden bands.	5	
14.	(a)	Explain the formation of $p$ - $n$ junction diode.	5	
	(b)	Describe the working of $p$ - $n$ junction diode with forward and reverse bias.	ard 5	
15.	(a)	Write the collector current expression in CE and CB models of a transistor in terms of $, I_B, I_E, I_C, I_{CBO}$ and $I_{CEO}$ .	ode 5	
	(b)	Compare the performance characteristics of CB, CE a CC configurations.	nd 5	
16.	(a)	Distinguish between avalanche and Zener breakdown.	5	
	(b)	Define and . Give the relationship between them.	5	
17.	Exp typ	plain the construction and working principle of deplet e of <i>n</i> -channel MOSFET. 5	ion 5+5=10	
18.	(a)	Describe the working of bridge rectifier circuit with inp and output waveforms.	out 8	
	(b)	Explain the need for a filter circuit in power supplies.	2	

2

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